



<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No. <b>LAM1P147/P0675</b>	Application No.: <b>09/782,185</b>
	Applicant: <b>ZHU et al.</b>	
	Filing Date <b>February 12, 2001</b>	Group <b>1765</b>

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
K-cc	A	5,970,376	10/19/99	Chen	438	637	12/29/97
K-cc	B	6,040,248	03/21/00	Chen et al.	438	725	06/24/98
	C						
	D						
	E						
	F						
	G						
	H						
	I						

#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
K-cc	J	09036089	02/07/97	Japan	H01L	21/3065	X	
	K							
	L							
	M							
	N							

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
K-cc	O	Eto et al., "High Selectivity Photoresist Ashing by the Addition of NH <sub>3</sub> to CF <sub>4</sub> /O <sub>2</sub> or CHF <sub>3</sub> /O <sub>2</sub> ", SID 99 Digest, pages 844-847
K-cc	P	Delsol et al., "Transformer Coupled Plasma Dielectric Etch for 0.25 $\mu$ m Technologies", Elsevier, Microelectronic Engineering 50 (2000), pages 75-80
K-cc	Q	International Search Report, 11/20/02
Examiner	K-cc. <i>[Signature]</i>	
	Date Considered 5-1-03	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.